

Type 2N3866A Geometry 1007 Polarity NPN

Qual Level: JAN - JANS

Generic Part Number: 2N3866A

REF: MIL-PRF-19500/398

Features:

 General-purpose silicon transistor for switching and amplifier applications.

- Housed in TO-39 case.
- Also available in chip form using the 1007 chip geometry.
- The Min and Max limits shown are per MIL-PRF-19500/398 which Semicoa meets in all cases.



Request Quotation

Maximum Ratings

 $T_C = 25^{\circ}C$ unless otherwise specified

Rating	Symbol	Rating	Unit	
Collector-Emitter Voltage	V _{CEO}	30	V	
Collector-Base Voltage	V _{CBO}	60	V	
Emitter-Base Voltage	V_{EBO}	3.5	V	
Collector Current, Continuous	I _C	0.4	А	
Operating Junction Temperature	TJ	-55 to +175	°C	
Storage Temperature	T _{STG}	-55 to +175	°C	



Electrical Characteristics

 $T_C = 25^{\circ}C$ unless otherwise specified

OFF Characteristics	Symbol	Min	Max	Unit
Collector-Base Breakdown Voltage $I_C = 100 \ \mu A$, pulsed	V _{(BR)CBO}	60		V
Collector-Emitter Breakdown Voltage $I_C = 5$ mA, pulsed	V _{(BR)CEO}	30		V
Collector-Emitter Breakdown Voltage $I_C = 40$ mA, $V_{BE} = -5V$, clamped	V _{(BR)CEC}	55		
Emitter-Base Breakdown Voltage $I_E = 100 \mu A$, pulsed	$V_{(BR)EBO}$	3.5		V
Collector-Emitter Cutoff Current $V_{CE} = 55 \text{ V}$	I _{CES}		100	μΑ
Collector-Emitter Cutoff Current $V_{CE} = 55 \text{ V}, T_A = +150^{\circ}\text{C}$	I _{CES2}		2.0	mA
Collector-Emitter Cutoff Current $V_{CE} = 28 \text{ V}$	I _{CEO}		20	μΑ

ON Characteristics	Symbol	Min	Max	Unit
Forward Current Transfer Ratio				
$I_C = 50 \text{ mA}, V_{CE} = 5.0 \text{ V (pulsed)}$	h _{FE1}	25	200	
$I_C = 360 \text{ mA}, V_{CE} = 5.0 \text{ V (pulsed)}$	h _{FE2}	8.0		
$I_C = 50 \text{ mA}, V_{CE} = 5.0 \text{ V (pulsed)}, T_A = -55^{\circ}\text{C}$	h _{FE3}	12		
Collector-Emitter Saturation Voltage				
$I_C = 100 \text{ mA}, I_B = 10 \text{ mA (pulsed)}$	$V_{CE(sat)}$		1.0	V dc
Power Output				
$V_{CC} = 28 \text{ V}, P_{IN} = 0.15 \text{ W}, f = 400 \text{ MHz}$	P _{1out}	1.0	2.0	W
Power Output				
$V_{CC} = 28 \text{ V}, P_{IN} = 0.075 \text{ W}, f = 400 \text{ MHz}$	P _{2out}	0.5		W
Collector Efficiency				
$V_{CC} = 28 \text{ V}, P_{IN} = 0.15 \text{ W}, f = 400 \text{ MHz}$	n ₁	45		%
Collector Efficiency				
$V_{CC} = 28 \text{ V}, P_{IN} = 0.075 \text{ W}, f = 400 \text{ MHz}$	n_2	40		%

Small Signal Characteristics	Symbol	Min	Max	Unit
$\label{eq:magnitude} \textit{Magnitude of Common Emitter, Small Signal, Short Circuit} \\ \textit{Current Transfer Ratio} \\ \textit{I}_{C} = 50 \text{ mA}, \textit{V}_{CE} = 15 \text{ V}, \textit{f} = 200 \\$	h _{FE}	4.0	7.5	
Open Circuit Output Capacitance $V_{CB} = 28 \text{ V}, I_E = 0$	C _{OBO}		3.5	pF